



Excellence in Electronics

TYPE 1N67

The 1N67 is a hermetically sealed point contact germanium diode designed for use in general purpose rectifier applications where very high back resistance, at least 1 megohm; small size, absence of heater voltage, low shunt capacitance, resistance to changes in humidity and temperature*, and excellent transient response are important. Operable at temperatures up to 100°C, the 1N67 can be heated as high as 125°C with no irreversible change in characteristics. Each diode is dynamically tested for hysteresis, drift, and flutter. The 1N67 has extremely uniform electrical characteristics and reliable mechanical stability.

MECHANICAL DATA

- TERMINALS:** Dumet wire, Tinned to within 1/8" of barrel
Diameter: 0.017" max. Length: 1" min.
- TERMINAL CONNECTIONS:** White Band at Cathode Terminal
- MOUNTING POSITION:** Any
- PLUG - IN EQUIVALENT:** Available as 1N67-P

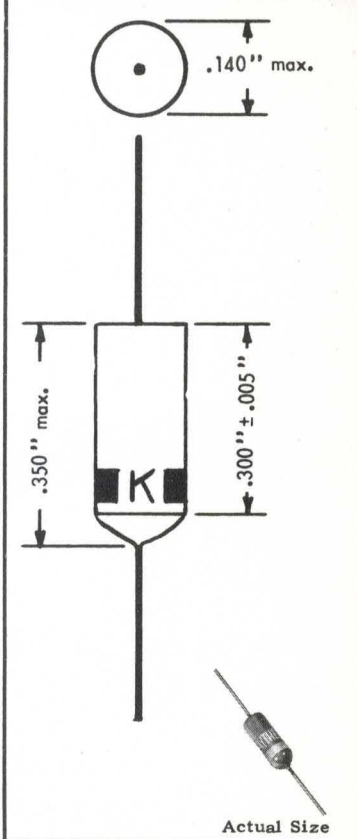
ELECTRICAL DATA

RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

Inverse Voltage	80 volts
Average Rectified Current	35 ma.
Peak Rectified Current	100 ma.
Surge Current (for 1 sec.)	500 ma.
Ambient Temperature Range	- 50 to + 100 °C
Dissipations at:	
25°C	80 mw.
50°C	65 mw.
75°C	50 mw.
100°C	30 mw.

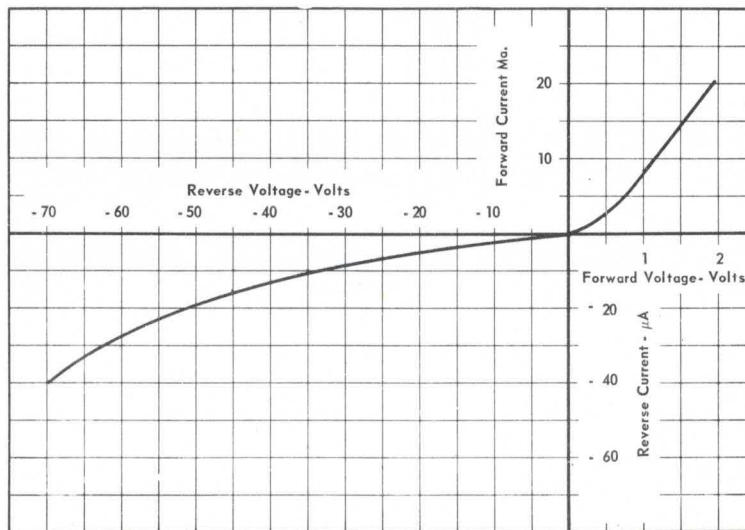
CHARACTERISTICS: (at 25°C)

Maximum Inverse Current at - 5 volts	5 µa.
Maximum Inverse Current at - 50 volts	50 µa.
Minimum Forward Current at + 1 volt	4.0 ma.
Shunt Capacitance	1.0 µufd.
Minimum Reverse Voltage for Zero Dynamic Resistance	100 volts



* Each diode receives repeated humidity cycling, and additional temperature cycling ranging from -25°C to 130°C.

TYPICAL STATIC CHARACTERISTICS (at 25°C)



Tentative Data